METHOD OF FORMING METAL FUSES IN CMOS PROCESSES WITH COPPER INTERCONNECT

ABSTRACT OF THE DISCLOSURE

The present invention provides a method of forming a semiconductor device fuse and a semiconductor device fuse structure. A first dielectric layer is formed on top of a metal layer in a semiconductor device. The dielectric layer is patterned to provide access to at least two contacts in the metal layer. A conductive metal layer is deposited and patterned to form a fuse between the fuse contacts. A second dielectric layer is deposited on the conductive metal layer.